TOSHIBA BIPOLAR LINEAR INTEGRATED CIRCUIT MULTI-CHIP

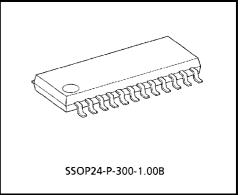
TA8461F

DUAL POWER OPERATIONAL AMPLIFIER

The TA8461F is a multiple chip IC consisting of 4 saturated voltage discrete transistors and 1 dual operational amplifier.

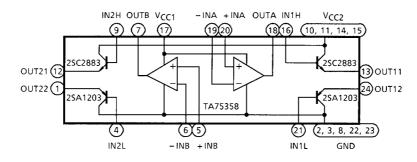
FEATURES

- Large Output Current : I_{OUT} = 1.5A (MAX.)
- Sealed in a Small Package : SSOP24



BLOCK DIAGRAM

Weight: 0.27 g (Typ.)



PIN CONNECTION

OUT22 [1	24] OUT12
GND [2	23] GND
GND [3	22] GND
IN2L	4	21	IN1L
+INB [5	20] + INA
-INB [6	19	
оитв [7	18] Ουτά
GND [8	17] v _{cc1}
IN2H [9	16] імтн
vcc₂ [10	15] v _{CC2}
vcc₂ [11	14] v _{cc₂}
ουτ21 [12	13] OUT11

PIN FUNCTION

PIN No.	SYMBOL	FUNCTIONAL DESCRIPTION			
1	OUT22	PNP (2) Emitter			
2	GND	GND			
3	GND	GND			
4	IN2L	PNP (2) Base			
5	+INB	OP. Amp (B) input (+)			
6	-INB	OP. Amp (B) input (-)			
7	OUTB	OP. Amp (B) output			
8	GND	GNB			
9	IN2H	NPN (2) Base			
10	V _{CC2}	Output transistor voltage supply			
11	V _{CC2}	Output transistor voltage supply			
12	OUT21	NPN (2) Emitter			
13	OUT11	NPN (1) Emitter			
14	V _{CC2}	Output transistor voltage supply			
15	V _{CC2}	Output transistor voltage supply			
16	IN1H	NPN (1) Base			
17	V _{CC1}	OP. Amp. voltage supply			
18	OUTA	OP. Amp. (A) output			
19	-INA	OP. Amp. (A) input (-)			
20	+INA	OP. Amp. (A) input (+)			
21	IN1L	PNP (1) Base			
22	GND	GND			
23	GND	GND			
24	OUT12	PNP (1) Emitter			

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Supply Voltage		V _{CC}	30	V
Output Transistor	Collecto-Base Voltage	V _{CBO}	30	V
	Collector-Emitter Voltage	V _{CEO}	30	V
	Emitter-Base Voltage	V _{EBO}	5	V
	Output Current	IOUT (AVE.)	1.5	А
	Output Current	IOUT (PEAK)	3.0 (Note 1)	A
	Base Current	Ι _Β	0.3	А
	Amplifier Differential Input Voltage	DVIN	30	V
OP. Amp.	Amplifier Input Voltage	VIN	30	V
Power Dissipation		PD	1.0 (Note 2)	W
Junction Temperature		Тj	125	°C
Operating Temperature		T _{opr}	-40~85	°C
Storage Temperature		T _{stg}	-55~125	°C

Note 1: Pulse measured:

Pulse width = 10 ms (MAX.)

Repetition cycle = 30% (MAX.)

Note 2: No heat sink

ELECTRICAL CHARACTERISTICS Output transistor unit (Ta = 25°C)

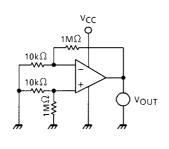
CHARACTERISTIC	SYMBOL	TEST CIRC UIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
DC Current Amplification Factor	h _{FE (1)}	_	V _{CE} = 2 V, I _C = 0.5 A	160		600	
	h _{FE (2)}	_	V _{CE} = 2 V, I _C = 1.5 A	50	100	—	
Output Saturation Voltage	V _{CE (sat)} (NPN)	—	I _C = 0.5 A, I _B = 10 mA	-	0.2	0.50	V
			I _C = 1.5 A, I _B = 30 mA	_	-	2.0	
	V _{CE (sat)} (PNP)	_	I _C = 0.5 A, I _B = 10 mA	_	0.2	0.50	
			I _C = 1.5 A, I _B = 30 mA	_	_	2.0	
Transition Frequency	f _T	_	V _{CE} = 2 V, I _C = 0.5A	_	120	_	MHz
Output Leakage Current	I _{OL} (NPN)	_	V _{CC} = 30 V	_	0	10	
	I _{OL} (PNP)	_	V _{CC} = 30 V	_	0	10	μA
Base-Emitter Voltage	V _{BE} (NPN)	_	V _{CE} = 2 V, I _C = 0.5 A	_	_	1.0	v
	V _{BE} (PNP)	_	V _{CE} = 2 V, I _C = 0.5 A	_	_	1.0	v

Operational amplifier unit (V_{CC} = 5 V, Ta = 25°C)

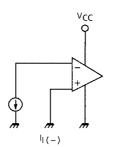
CHARACTERISTIC	SYMBOL	TEST CIR- CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Input Offset Voltage	V _{IO}	1	R _g ≤ 10 kΩ	_	2	7	mV
Input Offset Current	I _{IO}	2	—	-	5	50	nA
Input Bias Current	l	2	—	_	45	250	nA
In-Phase Input Voltage	CMVIN	3	V _{CC} = 30 V	0	_	V _{CC} −1.5	V
Supply Current	Icc	4	R _L = ∞, ALL OP Amps	_	0.7	1.2	mA
Voltage Gain	GV	5	R _L ≥ 2 kΩ	86	100		dB
Maximum Output Amplitude Voltage	V _{Op-p}	6	R _L = 2 kΩ	0	_	V _{CC} −1.5	V
Common Mode Rejection Ratio	CMRR	3	—	60	85	_	dB
Supply Voltage Rejection Ratio	SVRR	1	R _g ≤ 10 kΩ	60	100	_	dB
Source Current	I _{source}	6	$IN (-) = 0V_{DC}, IN (+) = 1V_{DC}$	20	40	_	mA
Sink Current	l _{sink}	6	$IN (-) = 0V_{DC}, IN (+) = 1V_{DC}$	10	20	_	mA
Cut-off Frequency	f _T	_	—	—	1.5	_	MHz
Slew Rate	S _R	—	—	—	0.8	—	V / µs

TEST CIRCUIT 1

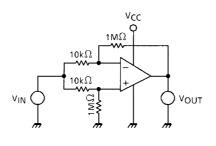
(1) V_{IO} , SVRR



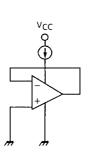
(2) II, IIO



(3) C_{MVIN}, C_{MRR}



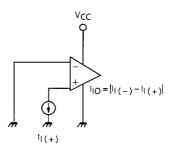
(4) Icc



- V_{IO} = V_{OUT} / 100
- SVRR = 20 log E (dB)

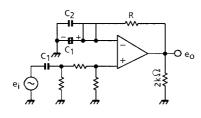
$$\mathsf{E} = \left| \frac{\mathsf{V}_{\mathsf{OUT1}} - \mathsf{V}_{\mathsf{OUT2}}}{\mathsf{V}_{\mathsf{CC1}} - \mathsf{V}_{\mathsf{CC2}}} \right| \times \frac{1}{100}$$

Vout1: Vout (V_{CC1} = 5 V) Vout2: Vout (V_{CC2} = 10 V)

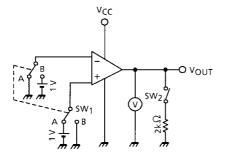


- CMRR = 20 log G_D / _{GC} (dB)
 G_D: Differential Voltage Gain
 G_C: In-phase Voltage Gain
- CMV_{IN} : V_{IN} = 0_V, V_{CC} 1.5 V
- I_{CC}: VCC = 5 V

(5) G_V



(6) V_{Op-p}, I_{source}, Isink



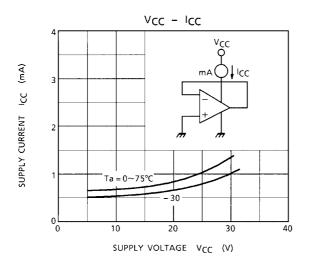
• G_V = 20 log _{eo} / _{ei} (dB)

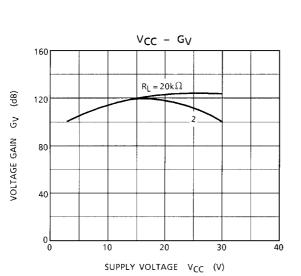
 $R > 1 / W_{C1}$

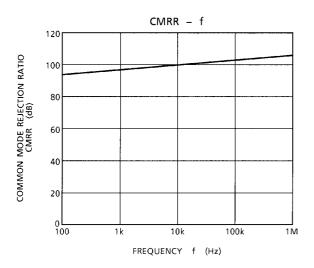
- $C_1: \ For \ Preventing \ DC \ Short-Circuit.$
- C₂ : For High Frequency Short-Circuit. Use a Mica or Titanium Capacitor.
- V_{Op-p} V_{OH} : SW₁ is to A side. V_{OL} : SW₁ is to B side.
- Isource SW_1 is to A side. $V_{OUT} \rightarrow 0 V$ Measurement
 - I_{sink} SW₁ is to B side. V_{OUT} \rightarrow 5 V Measurement

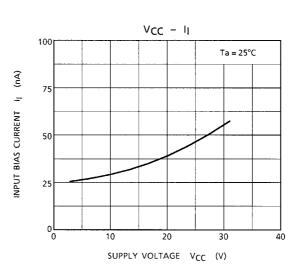
CHARACTERISTIC CURVES (Ta = 25°C)

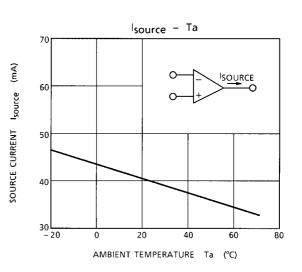
(1) Operational amplifier

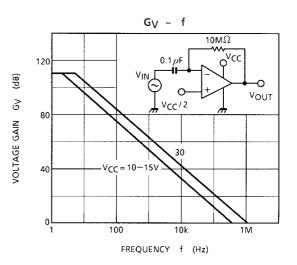


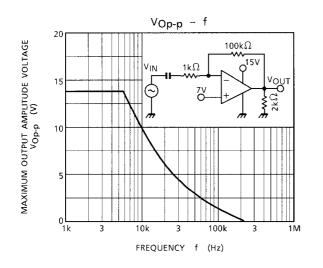


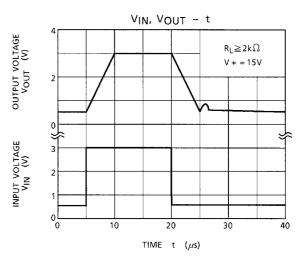


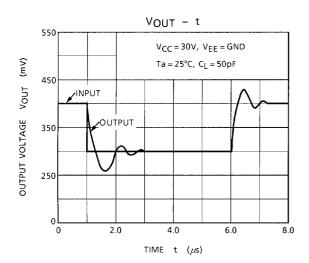


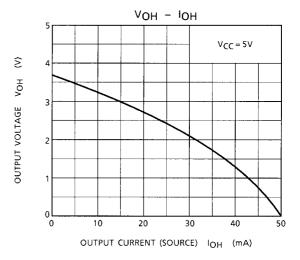


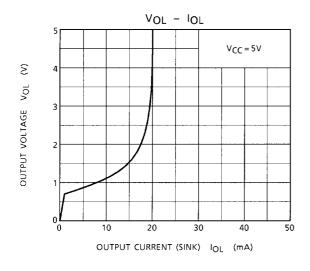




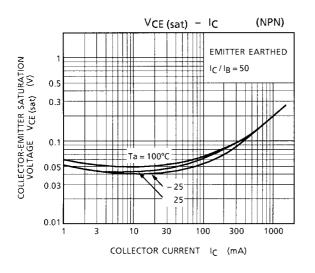


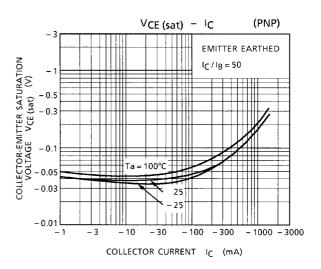


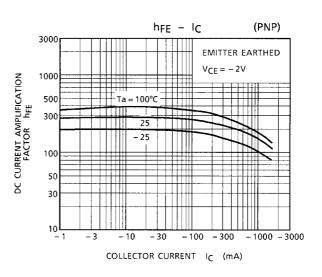


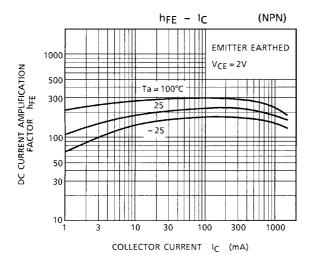


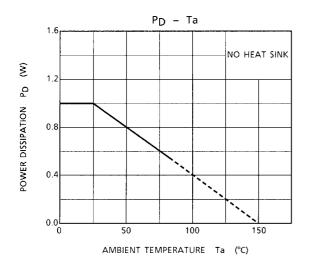
(2) NPN transistor, PNP transistor







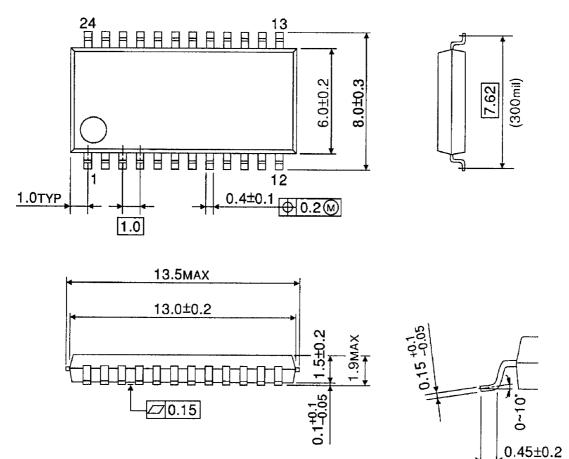




PACKAGE DIMENSIONS

SSOP24-P-300-1.00B

Unit : mm



Weight : 0.27 g (Typ.)

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Handbook" etc..

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